

Supplementary Materials

Highly Responsive, Broadband and Self-Powered Photodetector Based on PtSe₂/MoS₂ Heterostructure

Haoran Li ¹, Zhibin Yang *

Key Laboratory of Optoelectronic Information and Technology, Ministry of Education, and College of Precision Instrument and Optoelectronics Engineering, Tianjin University, Tianjin 300072, China

* Correspondence: zbyang0417@tju.edu.cn

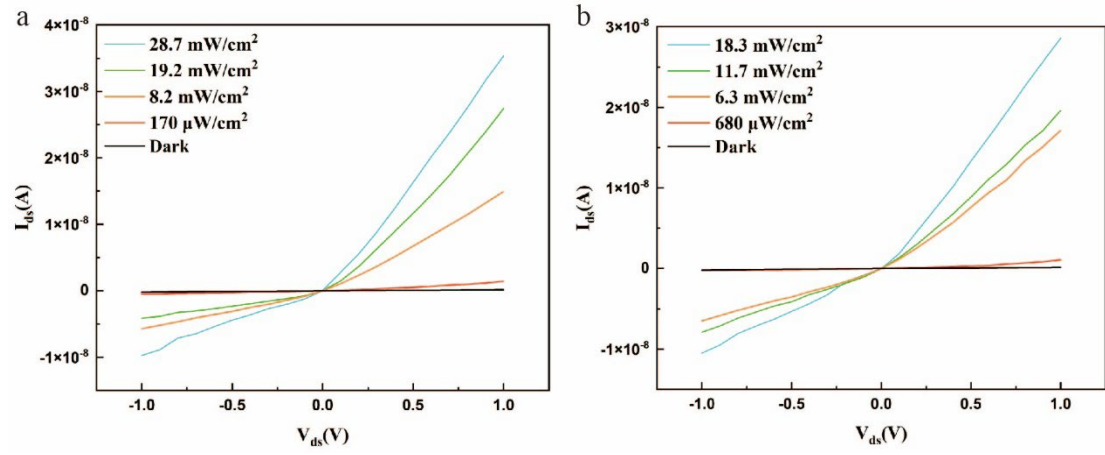


Figure S1. (a, b) The curves of I_{ds} - V_{ds} for PtSe₂/MoS₂ photodetector illuminated under 700 and 980 nm, respectively.

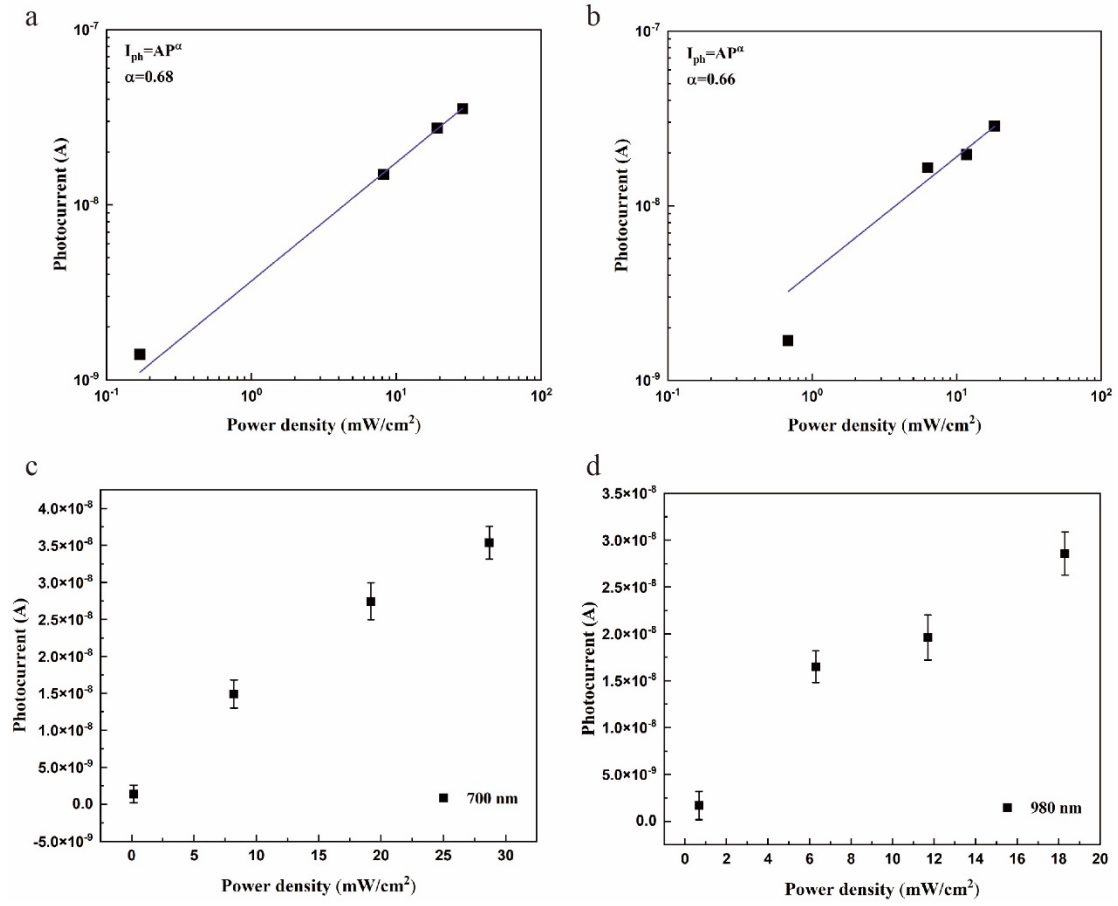


Figure S2. (a) Photocurrent as a function of power density ($V_{ds} = 1$ V, $\lambda = 700$ nm). (b) Photocurrent as a function of power density ($V_{ds} = 1$ V, $\lambda = 980$ nm). (c, d) Photocurrent of PtSe₂/MoS₂ heterostructure under 700 nm and 980 nm illumination. Error bars indicate the sample under multiple test.